

09/680,943

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	782	438/510	USPAT; EPO; JPO	2002/01/07 17:32
2	BRS	L2	112	p-type adj nitride	USPAT; EPO; JPO	2002/01/07 17:34
3	BRS	L3	40259	semiconductor adj layer	USPAT; EPO; JPO	2002/01/07 17:33
4	BRS	L4	8956	low adj resistivity	USPAT; EPO; JPO	2002/01/07 17:33
5	BRS	L5	47	hole adj carrier adj concentration	USPAT; EPO; JPO	2002/01/07 17:34
6	BRS	L6	86	p-type adj nitride adj semiconductor	USPAT; EPO; JPO	2002/01/07 17:36
7	BRS	L7	2	5 and 6      -5,959,307 (251) -5,777,350	USPAT; EPO; JPO	2002/01/07 17:37
8	BRS	L8	1	1 and 2      -6,043,140	USPAT; EPO; JPO	2002/01/07 17:37
9	BRS	L9	128	1 and 3	USPAT; EPO; JPO	2002/01/07 17:37
10	BRS	L10	11	4 and 5      -6,235,548	USPAT; EPO; JPO	2002/01/07 17:37
11	BRS	L11	0	1 and 6	USPAT; EPO; JPO	2002/01/07 17:38
12	BRS	L12	1072	3 and 4	USPAT; EPO; JPO	2002/01/07 17:38

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	0	1 and 3 and 4	USPAT; EPO; JPO	2002/01/07 17:38
14	BRS	L14	1	2 and 3 and 4 X	USPAT; EPO; JPO	2002/01/07 17:39
15	BRS	L15	2	2 and 4 -5,679,965 -5,237,182 (257)	USPAT; EPO; JPO	2002/01/07 17:39
16	BRS	L16	2	2 and 4 11	USPAT; EPO; JPO	2002/01/07 17:39
17	BRS	L17	2	2 and 5 U9	USPAT; EPO; JPO	2002/01/07 17:39
18	BRS	L18	86	2 and 6	USPAT; EPO; JPO	2002/01/07 17:39